

**Silicon NPN Power Transistors**

**BU608**

**DESCRIPTION**

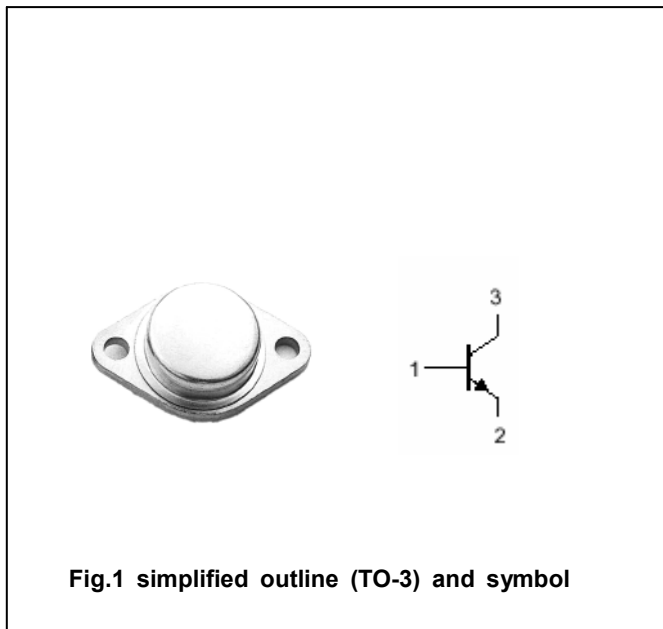
- With TO-3 package
- High voltage
- Wide area of safe operation

**APPLICATIONS**

- For TV horizontal deflection output applications

**PINNING (See Fig.2)**

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



**Absolute maximum ratings(Ta=25°C)**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V <sub>CBO</sub>	Collector-base voltage	Open emitter	400	V
V <sub>CEO</sub>	Collector-emitter voltage	Open base	200	V
V <sub>EBO</sub>	Emitter-base voltage	Open collector	7	V
I <sub>C</sub>	Collector current		7	A
P <sub>C</sub>	Collector power dissipation	T <sub>a</sub> =25°C	2.5	W
		T <sub>C</sub> =25°C	100	
T <sub>j</sub>	Junction temperature		200	°C
T <sub>stg</sub>	Storage temperature		-65~200	°C

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal resistance from junction to case	1.75	°C/W

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEQ(SUS)</sub>	Collector-emitter sustaining voltage	I <sub>C</sub> =100mA ; I <sub>B</sub> =0	200			V
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =1mA; I <sub>E</sub> =0	400			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =1mA; I <sub>C</sub> =0	7			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =6A ; I <sub>B</sub> =1.2A			1.0	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =6A ; I <sub>B</sub> =1.2A			1.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =400V; I <sub>E</sub> =0			10	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =5V; I <sub>C</sub> =0			10	μA
h <sub>FE-1</sub>	DC current gain	I <sub>C</sub> =1A ; V <sub>CE</sub> =5V	15			
h <sub>FE-2</sub>	DC current gain	I <sub>C</sub> =7A ; V <sub>CE</sub> =5V	5			

PACKAGE OUTLINE

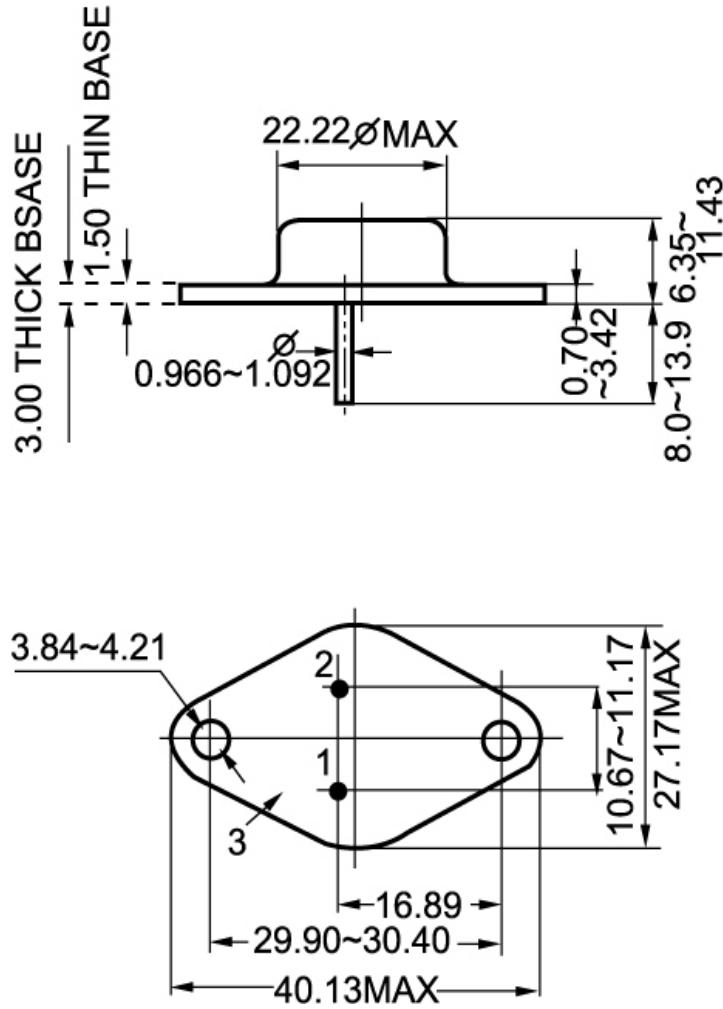


Fig.2 Outline dimensions